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Application Numb r	10/078,474
Filing Date	February 21, 2002
First Named Inventor	Hoki Kwon
Group Art Unit	2881
Examiner Name	t.b.d.
Attorney Docket Number	V637 02769 US

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
DW	\	International Search Report, dated 08-09-2003, relative to PCT application No. PCT/US 03/05368, the foreign equivalent to the instant U.S. application 10/078474.	
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